

S-LESD32L05T1G

ESD Protection Diode

1. FEATURES

- Low Capacitance
- Low Leakage
- ESD protection
- Complies with IEC 61000-4-2 standards:Air discharge:± 30kV

Contact discharge:±30kV

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S-prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.





2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping		
S-LESD32L05T1G	5E	3000/Tape&Reel		

3. MAXIMUM RATINGS(Ta = 25°C)

Parameter		Symbol	Limits	Unit
IEC 61000-4-2 (ESD)	Contact		± 30	kV
	Air		±30	
peak pulse power@8/20 µs(Note 1)		PPP	50	W
peak pulse current @8/20 µs(Note 1)		IPP	4	А
Storage Temperature Range		Tstg	-55~+150	٥C
Junction Temperature Range		TJ	-55~+150	°C

Note 1.Surge current waveform per Figure 1 according to IEC 61000-4-5.



4. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Symbol	Parameter	
IPP	Maximum Reverse Peak Pulse Current	
VC	Clamping Voltage @ IPP	
VRWM	Working Peak Reverse Voltage	
IR	Maximum Reverse Leakage Current @ VRWM	
VBR	Breakdown Voltage @ IT	
IT	Test Current	
IF	Forward Current	
VF	Forward Voltage @ IF	
Ppk	Peak Power Dissipation	
С	Capacitance @ VR = 0 and f = 1.0 MHz	



Uni-Directional TVS

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Reverse stand-off voltage	VRWM				5	V
Breakdown Voltage	VBR	IT = 1mA	5.5		8.5	V
Reverse leakage current	IR	VR = 5V			500	nA
Forward Voltage	VF	IF = 10mA			1.2	V
Clamping Voltage(Note 1)	VC1	IPP = 4A, tp=8/20µs			13	V
		IPP= 4 A, tp=100ns		9		
Clamping Voltage,TLP	VC2	IPP= 8 A, tp=100ns		11		V
		IPP= 16 A, tp=100ns		13		
Dynamic resistance	RDYN			0.4		Ω
Junction Capacitance	Cj	VR = 0V, f = 1MHz			0.8	pF

Note 1.Surge current waveform per Figure 1 according to IEC 61000-4-5.



6. ELECTRICAL CHARACTERISTICS CURVES





7.OUTLINE AND DIMENSIONS







SC70				
DIM	MIN	NOR	MAX	
А	0.80	0.95	1.00	
A1	0.00	0.05	0.10	
A2	0.7 REF			
b	0.30	0.35	0.40	
С	0.10	0.15	0.25	
D	1.80	2.05	2.20	
E	1.15	1.30	1.35	
е	1.20	1.30	1.40	
e1	0.65 BSC			
L	0.20	0.35	0.56	
He	2.00	2.10	2.40	
ALL Dimension in mm				

8.SOLDERING FOOTPRINT



SC70		
DIM	MIN	
А	1.90	
В	0.65	
С	0.65	
Х	0.70	
Y	0.90	



DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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